

● General Description

The AGM310M combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

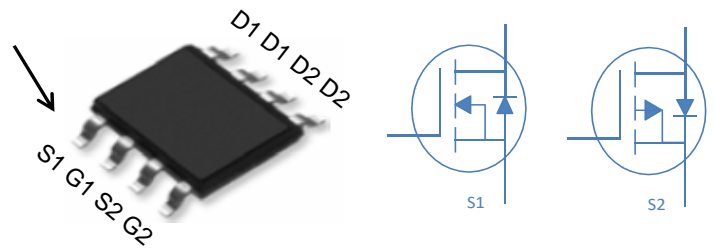
● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
30V	12mΩ	10A
-30V	17mΩ	-8A

SOP8 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM310M	AGM310M	SOP8	--mm	--mm	3000

Table 1. Absolute Maximum Ratings ($T_A=25^\circ\text{C}$)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	30	-30	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	± 20	V
I_D	Drain Current-Continuous($T_c=25^\circ\text{C}$) (Note 1)	10	-8.0	A
	Drain Current-Continuous($T_c=100^\circ\text{C}$)	6.5	-5.2	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	20	-18	A
P_D	Total Power Dissipation($T_c=25^\circ\text{C}$)	3.6	3.6	W
	Total Power Dissipation($T_A=100^\circ\text{C}$)	1.5	1.5	W
EAS	Avalanche energy (Note 3)	45	65	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	-55 To 150	$^\circ\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹	---	180	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	34	$^\circ\text{C/W}$

Table 3. N- Channel Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	30	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=30V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	1.6	2.5	V
gFS	Forward Transconductance	VDS=10V,ID=5A	--	10	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=15A	--	12	15	mΩ
		VGS=4.5V, ID=15A	--	15	22	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=15V,VGS=0V, F=1MHZ	--	850	--	pF
Coss	Output Capacitance		--	130	--	pF
Crss	Reverse Transfer Capacitance		--	98	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	1.9	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=15V, RL=0.75Ω,RGEN=6Ω	--	4.7	--	nS
tr	Turn-on Rise Time		--	11	--	nS
td(off)	Turn-Off Delay Time		--	17	--	nS
tf	Turn-Off Fall Time		--	5.6	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=15V, ID=10A	--	16	--	nC
Qgs	Gate-Source Charge		--	3	--	nC
Qgd	Gate-Drain Charge		--	3.8	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	10	A
VSD	Forward on Voltage	VGS=0V,IS=8A	--	--	1.2	V
trr	Reverse Recovery Time	IF=8A , dI/dt=100A/μs ,	--	--	--	ns
Qrr	Reverse Recovery Charge	TJ=25°C	--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

Table 3. P-Channel Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=-250μA	-30	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-24V,VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.2	-1.7	-2.3	V
gFS	Forward Transconductance	VDS=-5V,ID=-20A	--	30	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-20A	--	17	23.1	mΩ
		VGS=-4.5V, ID=-15A	--	26	32	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=-15V,VGS=0V, F=1MHZ	--	1380	--	pF
Coss	Output Capacitance		--	310	--	pF
Crss	Reverse Transfer Capacitance		--	237	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	9	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-15V, ID=-15A,RGEN=3.3Ω	--	8	--	nS
tr	Turn-on Rise Time		--	18	--	nS
td(off)	Turn-Off Delay Time		--	31.8	--	nS
tf	Turn-Off Fall Time		--	18.4	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-25V, ID=-12A	--	45	--	nC
Qgs	Gate-Source Charge		--	6.4	--	nC
Qgd	Gate-Drain Charge		--	9.0	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-8	A
VSD	Forward on Voltage	VGS=0V,IS=-1A	--	--	-1.2	V
trr	Reverse Recovery Time	IF=-1A , dl/dt=100A/μs , TJ=25°C	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes2.Repetitive Rating: Pulse width limited by maximum junction temperature Notes

3.EAS condition: TJ=25°C

●N Channel characteristics curve

Fig.1 Power Dissipation

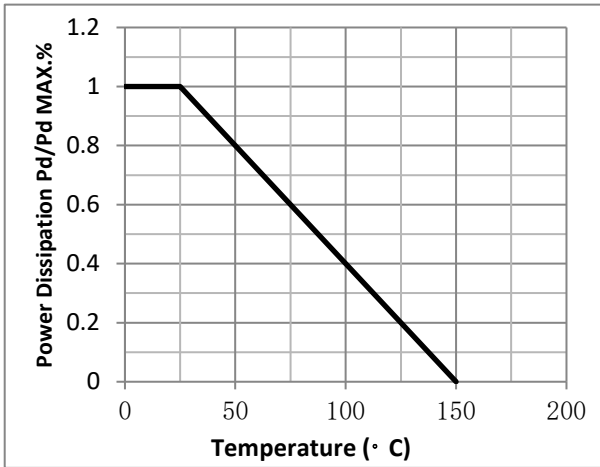


Fig.2 Typical output Characteristics

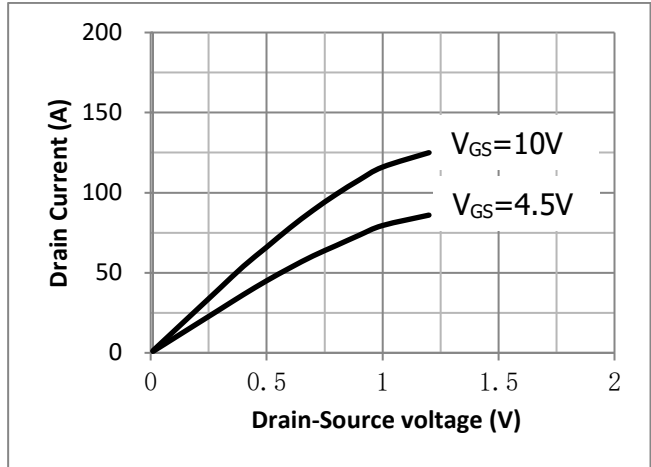


Fig.3 Threshold Voltage V.S Junction Temperature

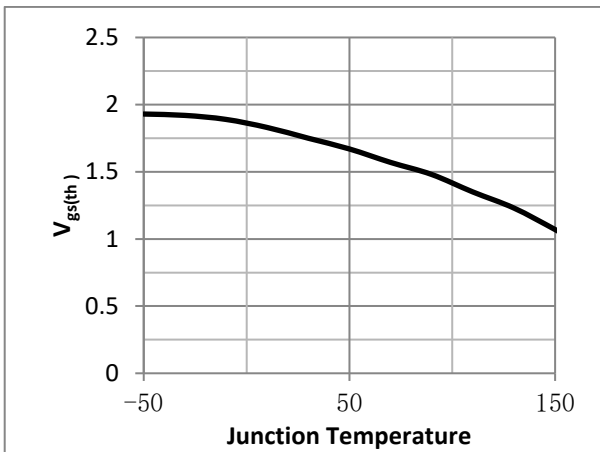


Fig.4 Resistance V.S Drain Current

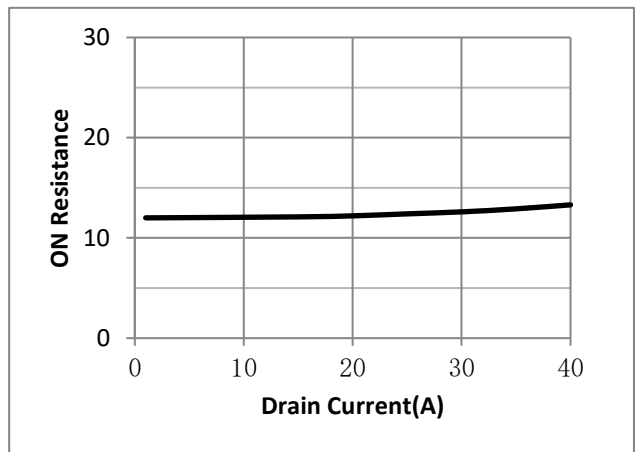


Fig.5 On-Resistance VS Gate Source Voltage

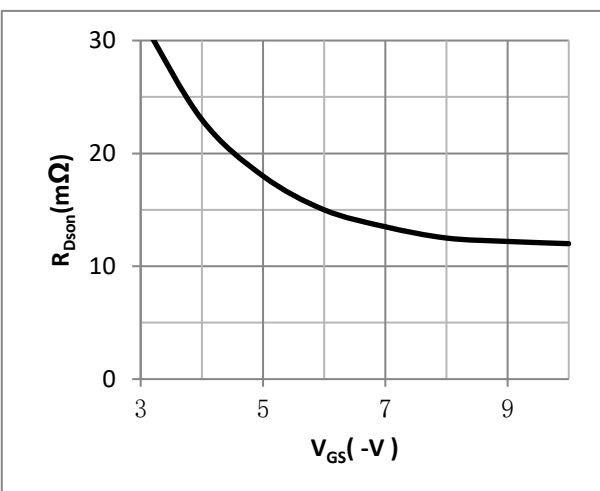
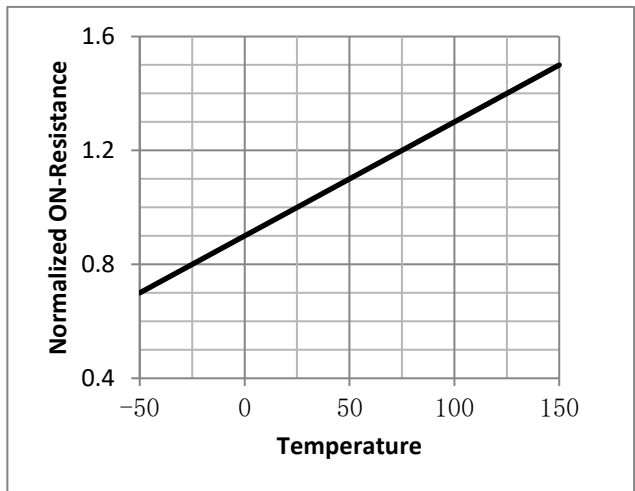


Fig.6 On-Resistance V.S Junction Temperature



•Test Circuit CHANNEL-N

Fig.1 Switching Time Measurement Circuit

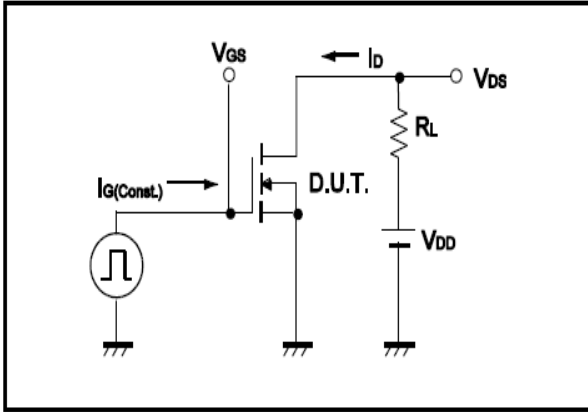


Fig.2 Gate Charge Waveform

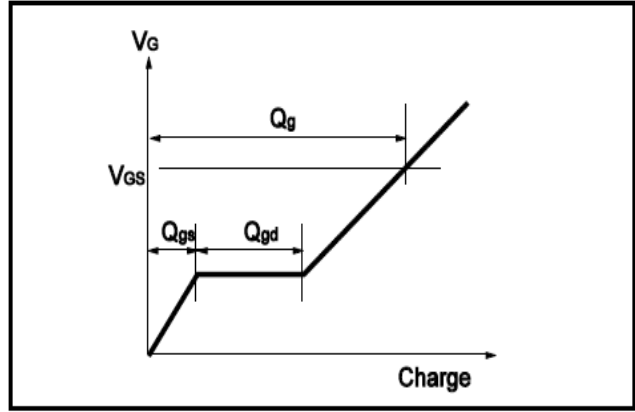


Fig.3 Switching Time Measurement Circuit

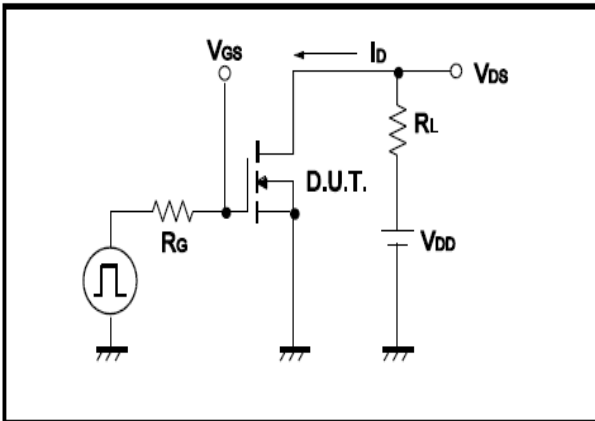


Fig.4 Gate Charge Waveform

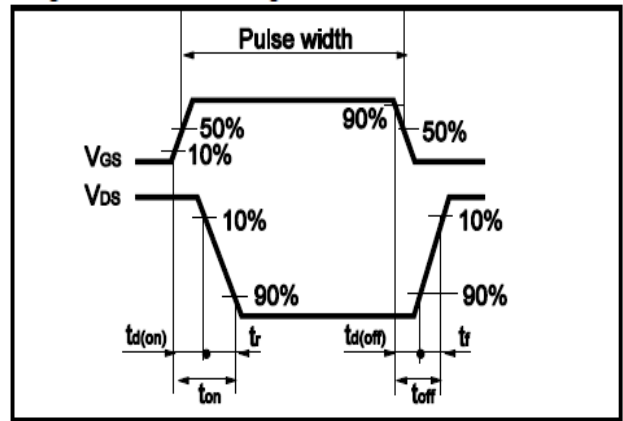


Fig.5 Avalanche Measurement Circuit

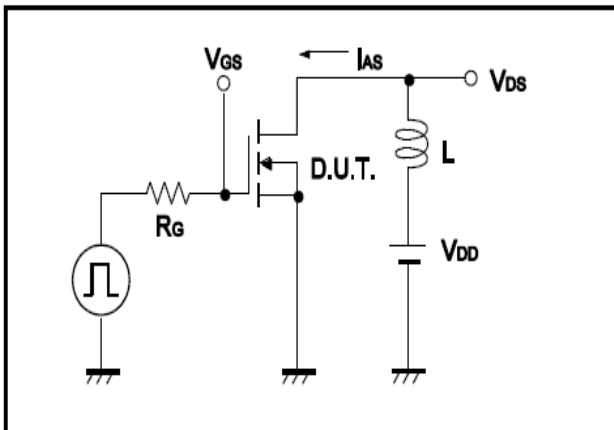
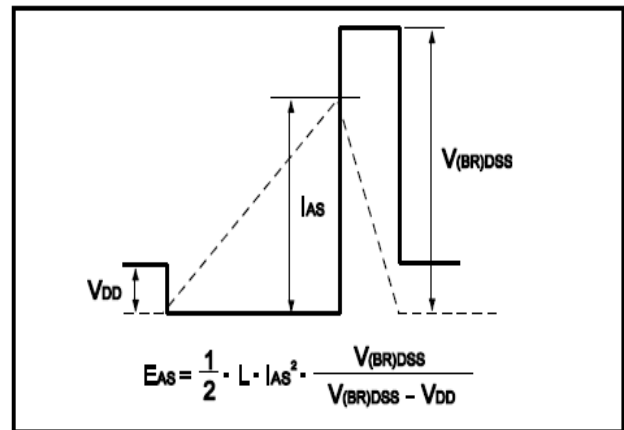


Fig.6 Avalanche Waveform



● P Channel characteristics curve

Fig.1 Power Dissipation Derating Curve

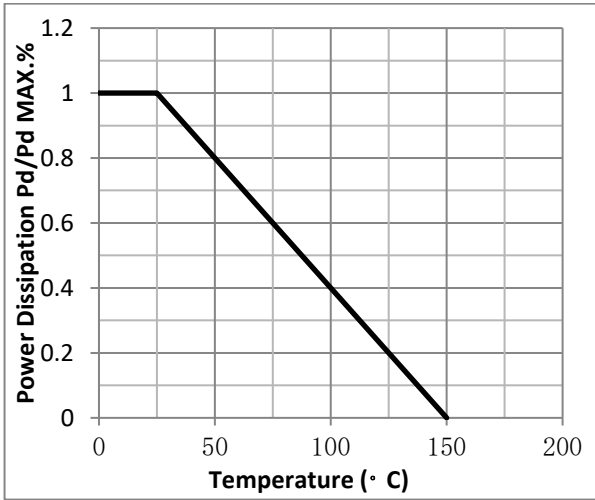


Fig.2 Typical output Characteristics

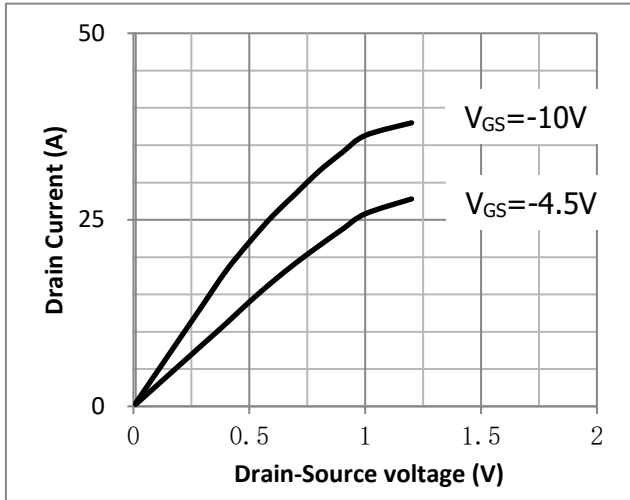


Fig.3 Threshold Voltage V.S Junction Temperature

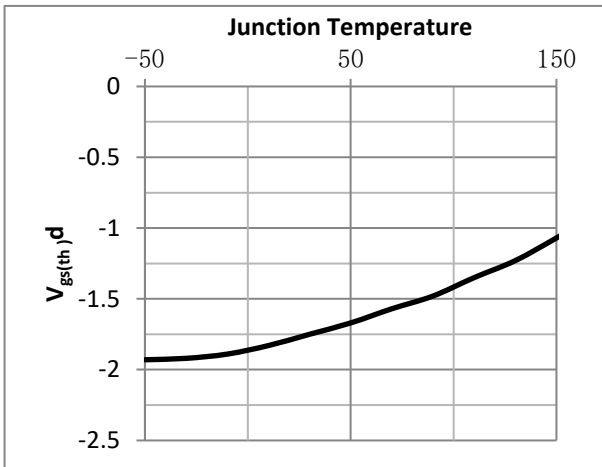


Fig.4 Resistance V.S Drain Current

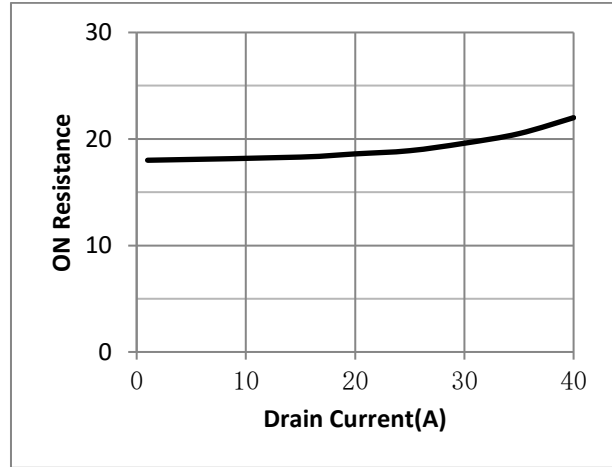


Fig.5 On-Resistance VS Gate Source Voltage

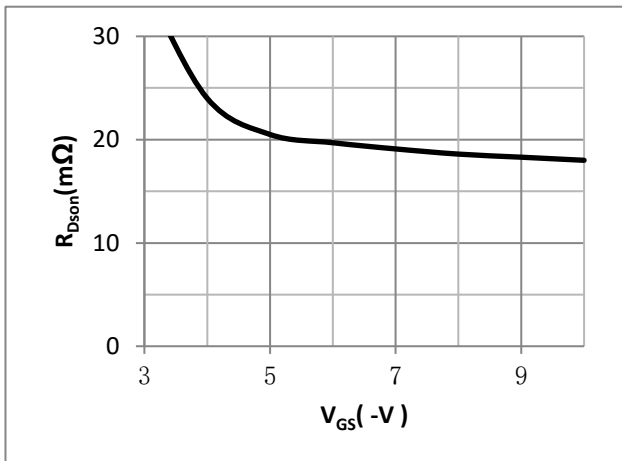
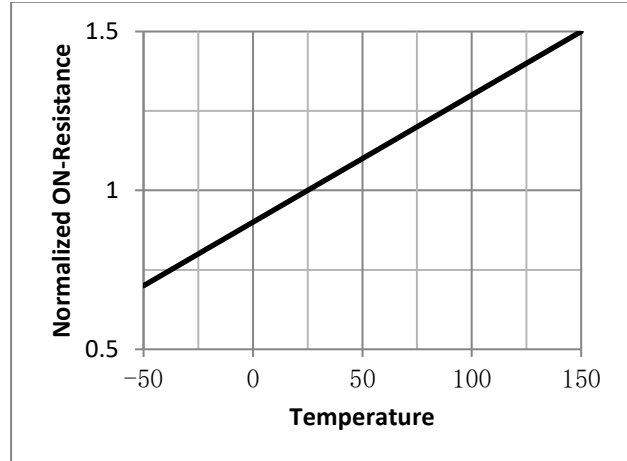


Fig.6 On-Resistance V.S Junction Temperature



•Test Circuit CHANNEL-P

Fig.7 Switching Time Measurement Circuit

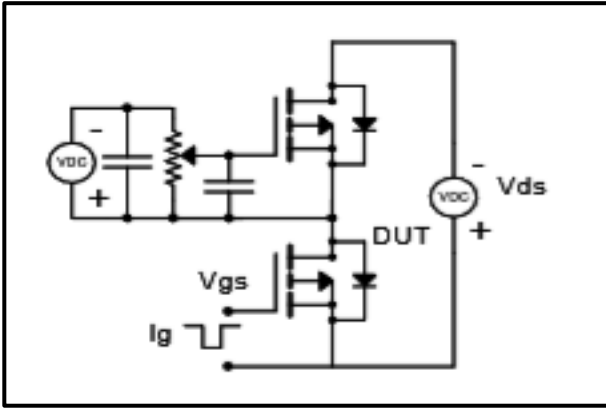


Fig.8 Gate Charge Waveform

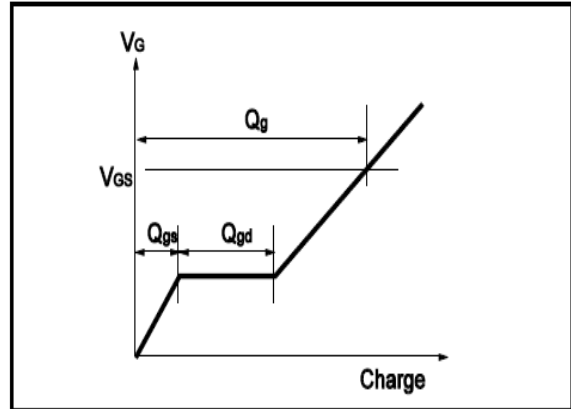


Fig.9 Switching Time Measurement Circuit

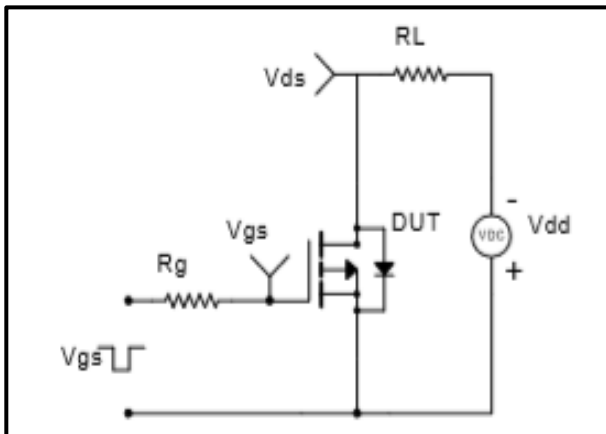


Fig.10 Gate Charge Waveform

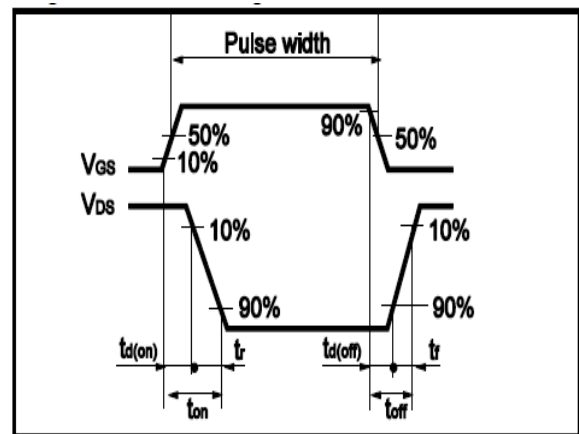


Fig.11 Avalanche Measurement Circuit

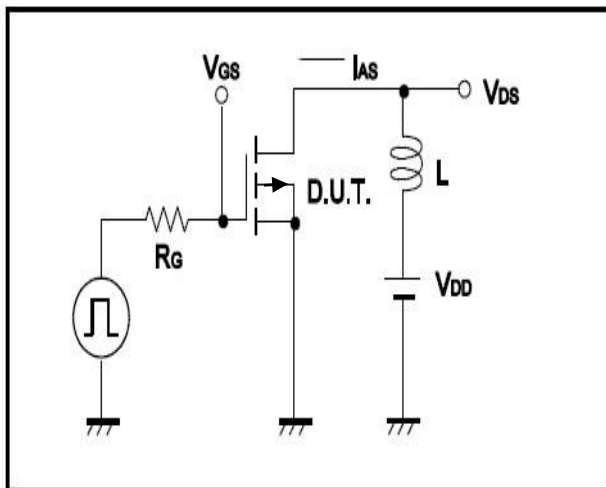
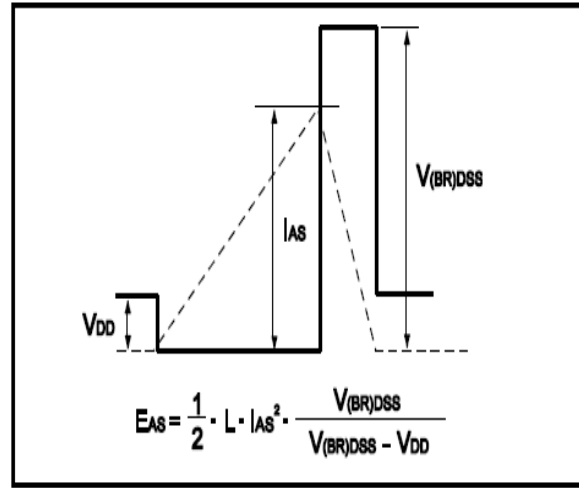


Fig.12 Avalanche Waveform




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